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Applicant: Atakov, et al. Docket: 200308123-4

Application No.: 10/676,443 Examiner: ARBES, Carl J.

(Continuation of Application No.: 09/735,566

Filed: 10/01/2003 Art Unit: 3729

For: Method of Forming Electrical Interconnects
 Having Electromigration-Inhibiting Plugs

As discussed by telephone today, I am sending for entry into the present application, a copy of page 24 of parent application 09/735,566 filed with this continuation application on 10/01/2003. It appears page 24 inadvertently was omitted from the submitted application papers in the present continuation application.

The continuation transmittal includes a statement: "This is a continuation of copending application number 09/735,566 filed on 12/12/2000 which is hereby incorporated by reference." Consequently, as provided by MPEP 201.06c), the accompanying copy of page 24 of application 09/735,566 may be entered in the present application.

If there are any questions, please call the undersigned attorney.

Date: March 7, 2005
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Respectfully submitted,


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conductive segments 110 forming electrical conductors 111, as shown in FIG. 4E.

Alternatively, liner 28 is not removed. Then, photomask, not shown, is used to remove liner 28 from the 5 portions of the dielectric layer 112 surrounding the slots 120 to form electrically isolated parallel conductors 111, as shown in FIG. 4E.

Other embodiments are within the spirit and scope of the appended claims. For example, considering the 10 embodiment described above in connection with FIGS. 1A through 1D, if a conductive underlayer, such as conductive underlayer 200 in FIG. 5, is used beneath the relatively high electrically conductive layer 24, the window 25 need only be etched through the layer 24 to the underlayer 200, 15 as shown in FIG. 5.

What is claimed is: